Ordering number : ENN7367

NPN Epitaxial Planar Silicon Transistor

30C02SS

Low-Frequency General-Purpose Amplifier Applications

Applications

- Low-frequency Amplifier, high-speed switching, small motor drive.

Features

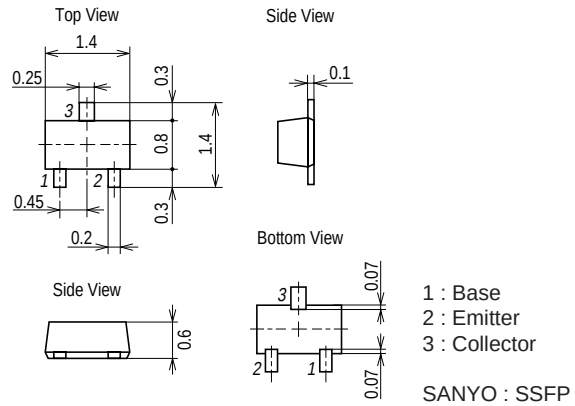
- Large current capacitance.
- Low collector-to-emitter saturation voltage (resistance). R_{CE}(sat) typ=330mΩ[I_C=0.7A, I_B=35mA].
- Ultrasmall package facilitates miniaturization in end products.
- Small ON-resistance (Ron).

Package Dimensions

unit : mm

2159A

[30C02SS]



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		40	V
Collector-to-Emitter Voltage	V_{CEO}		30	V
Emitter-to-Base Voltage	V_{EBO}		5	V
Collector Current	I_C		600	mA
Collector Current (Pulse)	I_{CP}		1.2	A
Collector Dissipation	P_C	Mounted on a glass-epoxy board (20×30×1.6mm)	200	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=30V, I_E=0			100	nA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0			100	nA
DC Current Gain	h_{FE}	V_{CE}=2V, I_C=50mA	300		800	
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=50mA		540		MHz

Marking : YM

Continued on next page.

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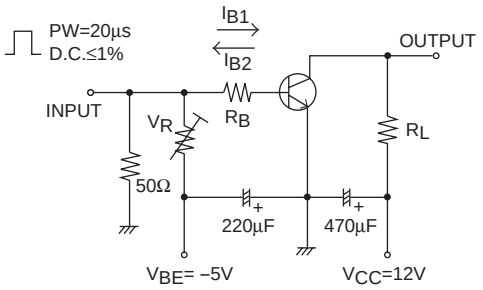
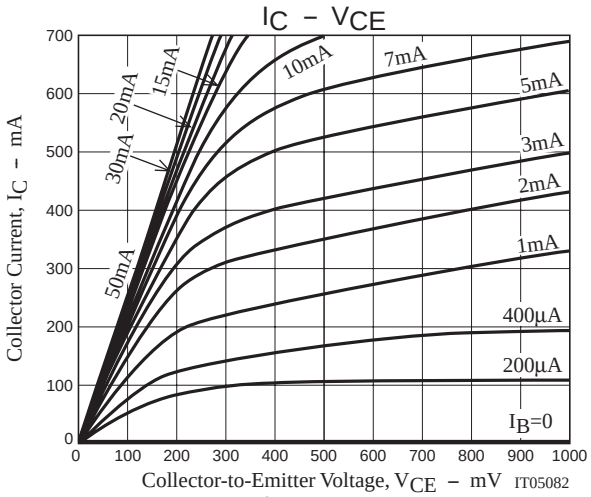
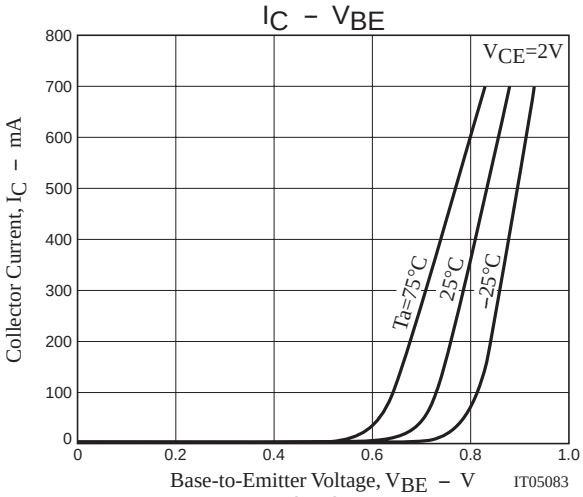
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Output Capacitance	Cob	V_{CB}=10V, f=1MHz		3.3		pF
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=200mA, I_B=10mA		85	190	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=200mA, I_B=10mA		0.9	1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0	40			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	30			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	5			V
Turn-ON Time	t_{on}	See specified Test Circuit.		35		ns
Storage Time	t_{stg}	See specified Test Circuit.		255		ns
Fall Time	t_f	See specified Test Circuit.		45		ns

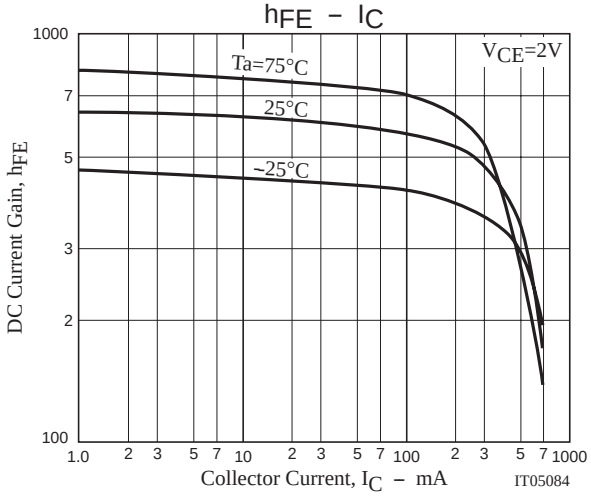
Switching Time Test Circuit

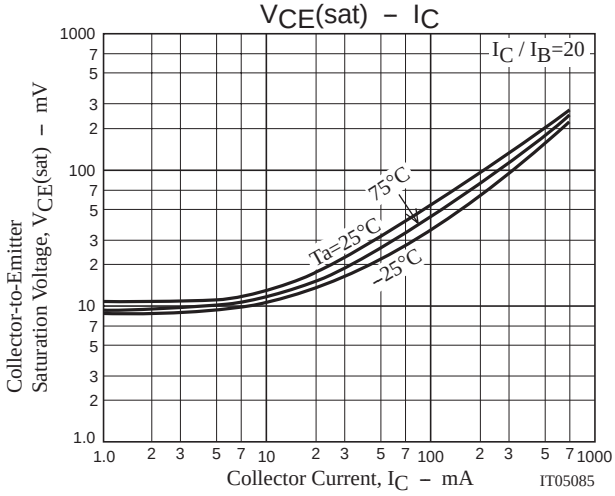


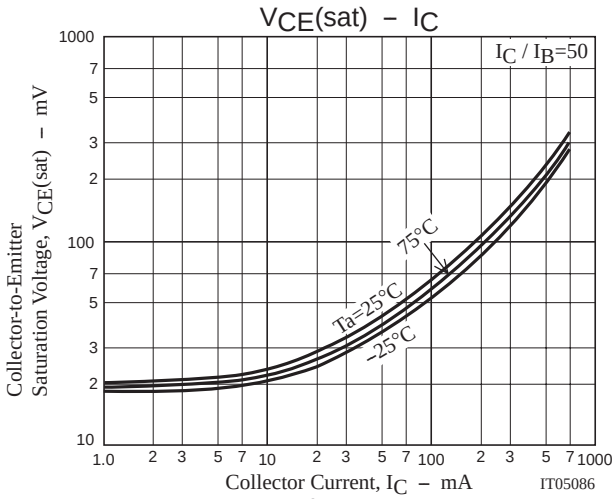
$20I_{B1}$= −$20I_{B2}$=I_C=300mA

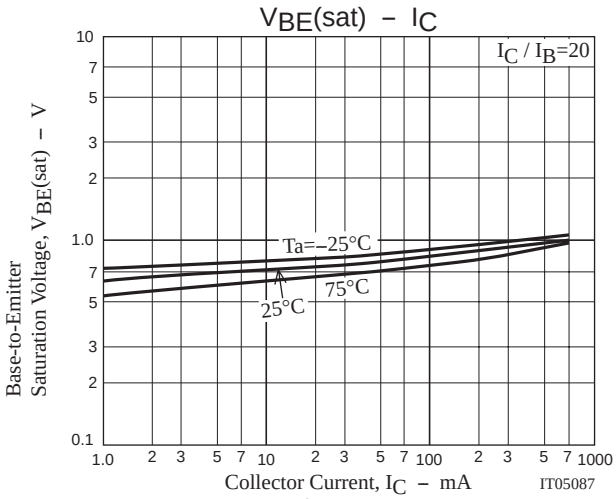


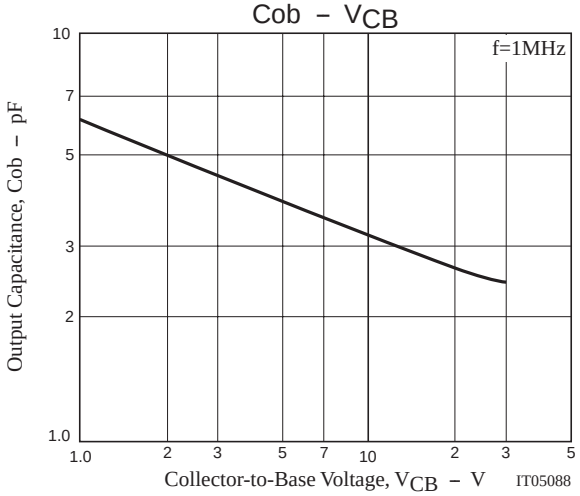


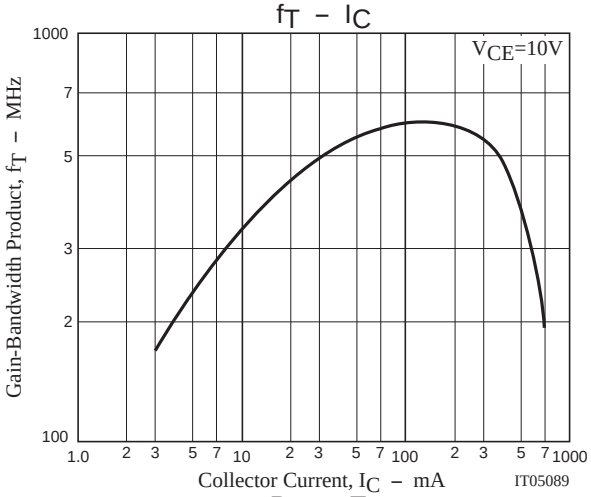


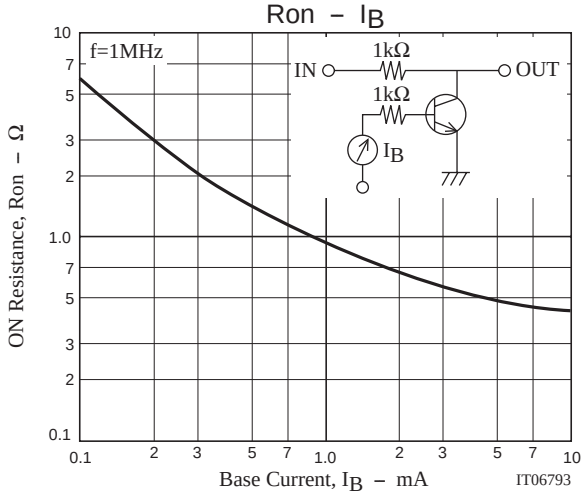


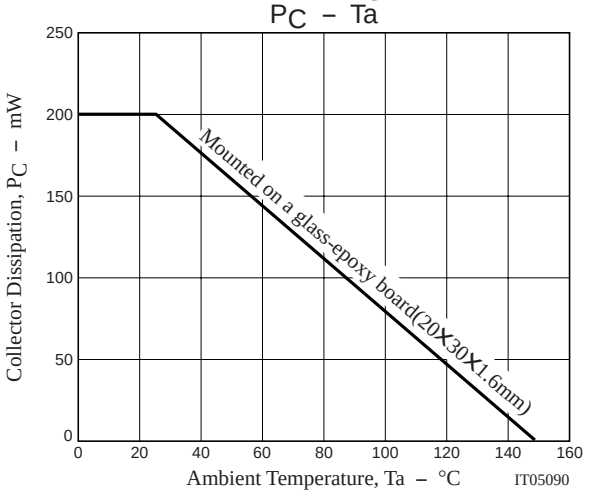

VCE(sat) – IC
IC / IB=50
75°C
Ta=25°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – mV
Collector Current, IC – mA
IT05086


VBE(sat) – IC
IC / IB=20
Ta=–25°C
25°C
75°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – mA
IT05087


Cob – VCB
f=1MHz
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
IT05088


fT – IC
VCE=10V
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – mA
IT05089


Ron – IB
f=1MHz
IN
1kΩ
1kΩ
OUT
IB
ON Resistance, Ron – Ω
Base Current, IB – mA
IT06793


PC – Ta
Mounted on a glass-epoxy board(20X30X1.6mm)
Collector Dissipation, PC – mW
Ambient Temperature, Ta – °C
IT05090